

# Efficient Power Conversion Corporation's (EPC) Monolithic Half-Bridge eGaN® Transistor Family Named Product of the Year by Electronic Products Magazine

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By: Herald Online

EL SEGUNDO, CALIF. — Efficient Power Conversion Corporation's (EPC) enhancement-mode gallium nitride on silicon (eGaN®) monolithic half-bridge power transistor products have been honored with an *Electronic Products* ' Product of the Year award.

The editors of *Electronic Products* — a leading trade publication for electronic design engineers — evaluated thousands of products launched in 2014. The winning products were selected on the basis of innovative design, significant advancement in technology or application, and substantial achievement in price and performance. The eGaN half bridges demonstrated success in the category of discrete semiconductors by being the first commercially available enhancement-mode single chip transistor half bridge.

"The EPC2100 family of half-bridge products represent a significant step in the emergence of gallium nitride semiconductor technology," said Paul O'Shea, Senior Editor for *Electronic Products Magazine*. "By integrating two eGaN power FETs into a single device, interconnect inductances and the interstitial space needed on the PCB are eliminated. This increases both efficiency (especially at higher frequencies) and power density, while reducing assembly costs to the end user's power conversion system."

"We are very proud that the editors of *Electronic Products* have selected the EPC2100 eGaN half-bridge products for this prestigious award. This award substantiates that gallium nitride technology continues to emerge as the performance leader in power conversion technology. We believe that silicon-based MOSFETs have reached the end of the road, and that eGaN technology will lead the way for continued increases in performance in power management," said Alex Lidow, EPC's co-founder and Chief Executive Officer.

The 2014 Product of the Year Awards were announced in the January 2015 issue of *Electronic Products* with a cover feature and a brief description of each product. Additionally, the winning products appear on *Electronic Products* ' website [http://www.electronicproducts.com/Discrete\\_Semiconductors/Transistors\\_Diodes/First\\_GaN\\_half\\_bridge\\_transistor\\_integrates\\_two\\_GaN\\_FETs.aspx](http://www.electronicproducts.com/Discrete_Semiconductors/Transistors_Diodes/First_GaN_half_bridge_transistor_integrates_two_GaN_FETs.aspx)

2014 marks the 39th annual *Electronic Products* ' "Product of the Year" Awards, recognizing the best products in the industry.